

DESCRIPTION

Title of Invention

PLASMA PROCESSING APPARATUS AND METHOD FOR CONTROLLING
SOURCE FREQUENCY OF SOURCE RADIO-FREQUENCY POWER

Technical Field

[0001]

Exemplary embodiments of the present disclosure relate to a plasma processing apparatus and a method for controlling the source frequency of source radio-frequency (RF) power.

Background

[0002]

Plasma processing is performed on substrates using a plasma processing apparatus. The plasma processing apparatus uses bias RF power to draw ions in plasma generated in a chamber toward a substrate. Patent Document 1 below describes a plasma processing apparatus that modulates the power level and the frequency of bias RF power.

Prior Art Document

Patent Document

[0003]

Patent Document 1: Japanese Patent Laid-Open Publication No. 2009-246091

Summary of the Invention